



Paper #12 (IDS)

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| | | | | Application Number | 09/943,187 |
| | | | | Filing Date | August 29, 2001 |
| | | | | First Named Inventor | Kristy A. Campbell, et al. |
| | | | | Art Unit | 2822 |
| | | | | Examiner Name | Khanh B. Duong |
| Sheet | 1 | of | 8 | Attorney Docket Number | M4065.0703/P703 |

| U.S. PATENT DOCUMENTS | | | | | |
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| Examiner Initials* | Cite No. ¹ | Document Number | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
| | | Number-Kind Code ² (if known) | | | |
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| KBD ↓ | BA | WO 97/48032 | 12/18/1997 | Kozicki et al. | |
| | BB | WO 99/28914 | 06/10/1999 | Kozicki et al. | |

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*EXAMINER: Initial reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.



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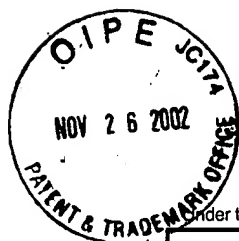
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| Sheet | 2 | of | 8 | Attorney Docket Number | M4065.0703/P703 |

| OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS | | |
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| Examiner Initials | Cite No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published. |
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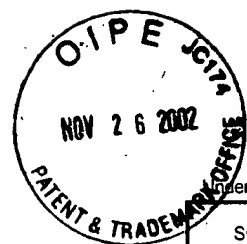
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| | | | Examiner Name | Khanh B. Duong | |
| Sheet | 6 | of | 8 | Attorney Docket Number | M4065.0703/P703 |

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| | | | First Named Inventor | Kristy A. Campbell, et al. | |
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